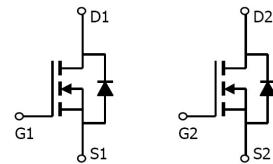


## Feature

- 60V,7A  
 $R_{DS(ON)} < 21m\Omega @ V_{GS}=10V$  TYP:17 m  $\Omega$   
 $R_{DS(ON)} < 28m\Omega @ V_{GS}=4.5V$  TYP:22 m  $\Omega$
- Trench DMOS Power MOSFET
- Fast Switching
- Exceptional on-resistance and maximum DC current capability



Schematic diagram



Marking and pin assignment

## Application

- DC/DC Converter
- Load Switch for Portable Devices
- Battery Switch

## Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity (PCS)
4847	AP4847	SOP-8	13 inch	-	4000

## ABSOLUTE MAXIMUM RATINGS ( $T_a=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current ( $T_a = 25^\circ C$ )	$I_D$	7	A
Continuous Drain Current ( $T_a = 100^\circ C$ )	$I_D$	5.2	A
Pulsed Drain Current <sup>(1)</sup>	$I_{DM}$	25	A
Power Dissipation	$P_D$	2	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	62.5	$^\circ C/W$
Junction Temperature	$T_J$	150	$^\circ C$
Storage Temperature	$T_{STG}$	-55~+150	$^\circ C$

**MOSFET ELECTRICAL CHARACTERISTICS( $T_a=25^\circ C$  unless otherwise noted)**

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
<b>Static Characteristics</b>						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	60	-	-	V
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = 60V, V_{GS} = 0V$	-	-	1	$\mu A$
Gate-body leakage current	$I_{GSS}$	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	$\pm 100$	nA
Gate threshold voltage <sup>(2)</sup>	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1	1.6	2.5	V
Drain-source on-resistance <sup>(2)</sup>	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 7A$	-	17	21	$m\Omega$
		$V_{GS} = 4.5V, I_D = 5A$	-	22	28	
<b>Dynamic characteristics</b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 30V, V_{GS} = 0V, f = 1MHz$	-	1115	-	$pF$
Output Capacitance	$C_{oss}$		-	91	-	
Reverse Transfer Capacitance	$C_{rss}$		-	82	-	
<b>Switching characteristics</b>						
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 30V, I_D = 7A$ $V_{GS} = 10V, R_G = 6\Omega$	-	5.9	-	ns
Turn-on rise time	$t_r$		-	9.1	-	
Turn-off delay time	$t_{d(off)}$		-	35	-	
Turn-off fall time	$t_f$		-	12	-	
Total Gate Charge	$Q_g$	$V_{DS} = 30V, I_D = 7A,$ $V_{GS} = 10V$	-	27	-	nC
Gate-Source Charge	$Q_{gs}$		-	2.9	-	
Gate-Drain Charge	$Q_{gd}$		-	7.6	-	
<b>Source-Drain Diode characteristics</b>						
Diode Forward voltage <sup>(2)</sup>	$V_{DS}$	$V_{GS} = 0V, I_s = 57$	-	-	1.2	V
Diode Forward current <sup>(3)</sup>	$I_s$		-	-	7	A
Reverse recovery time	$T_{rr}$	$I_s = 7A, V_{GS} = 0V, dI_F/dt = 100A/\mu s$		27		ns
Reverse recovery charge	$Q_{rr}$	$I_s = 7A, V_{GS} = 0V, dI_F/dt = 100A/\mu s$		23		nC

**Notes:**

1. Repetitive Rating: pulse width limited by maximum junction temperature
2. Pulse Test: pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$
3. Surface Mounted on FR4 Board,  $t \leq 10$  sec

**Typical Characteristics** (@  $T_J = 25^\circ\text{C}$ , unless otherwise specified.)

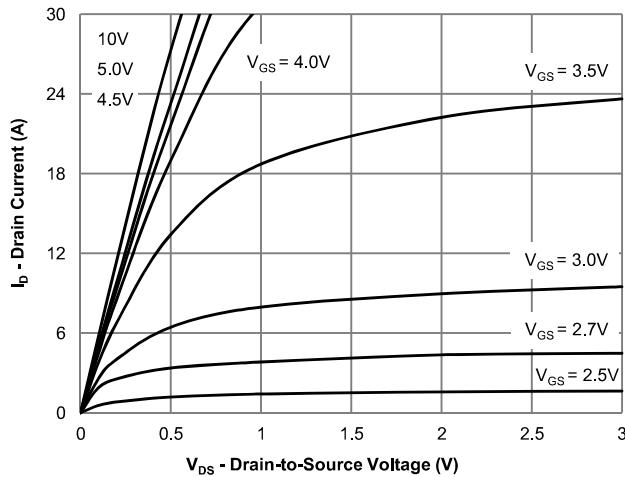


Figure 1: Output Characteristics

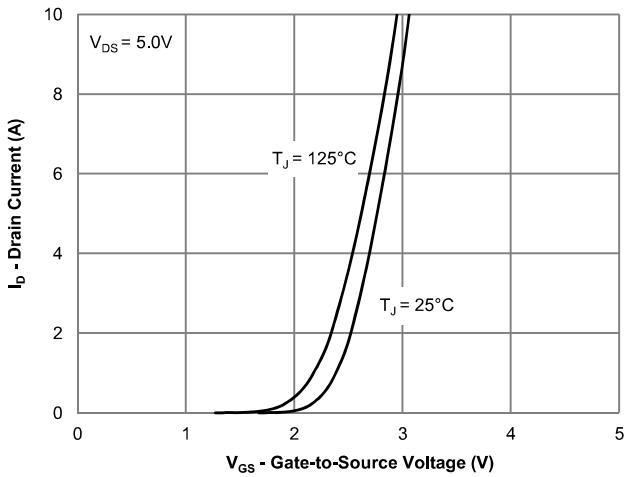


Figure 2: Transfer Characteristics

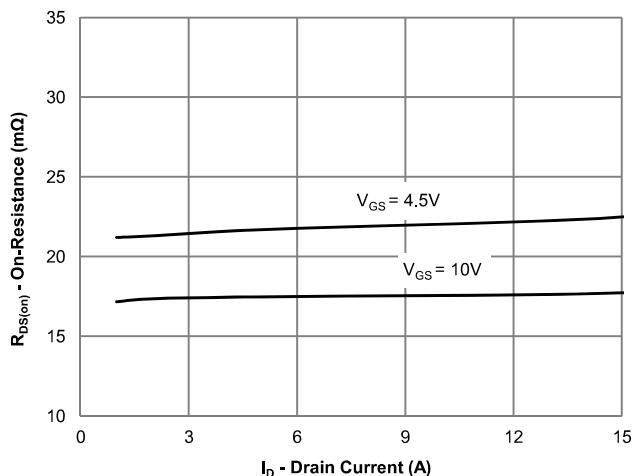


Figure 3: On-Resistance vs. Gate-Source Voltage

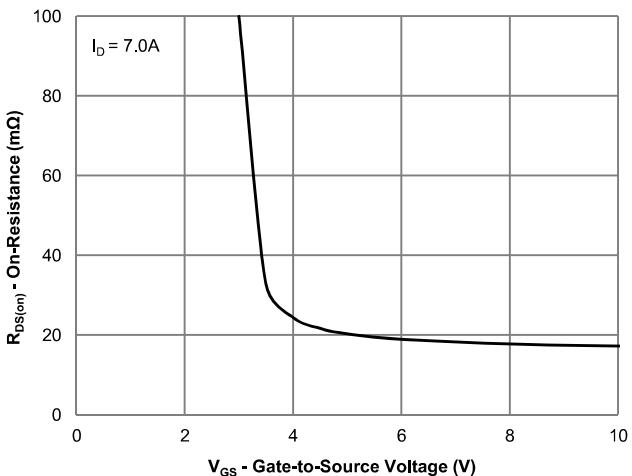


Figure 4: On-Resistance vs. Gate-Source Voltage

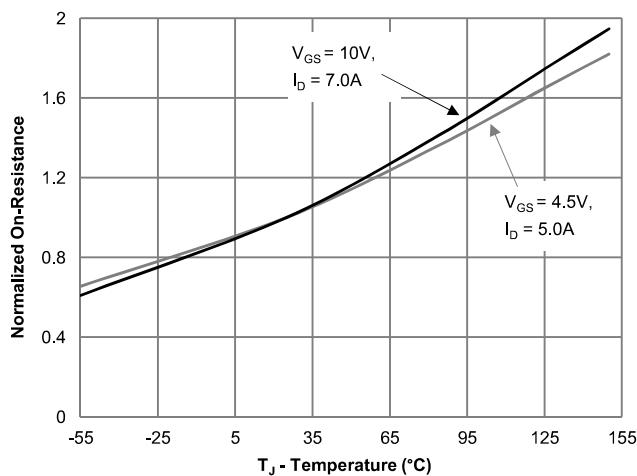


Figure 5: On-Resistance vs. Junction Temperature

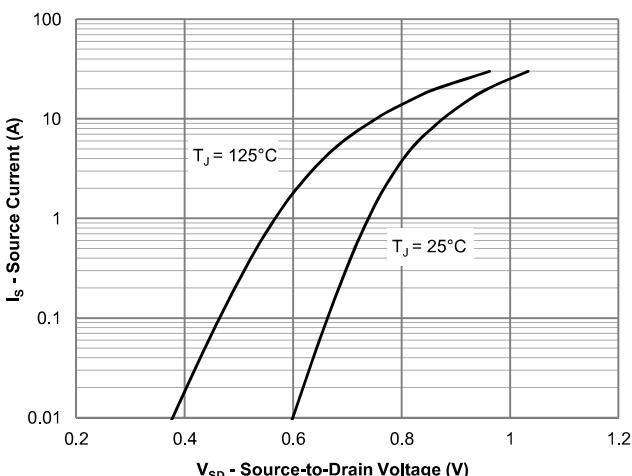


Figure 6: Source-Drain Diode Forward Voltage

**Typical Characteristics** (@  $T_J = 25^\circ\text{C}$ , unless otherwise specified.)

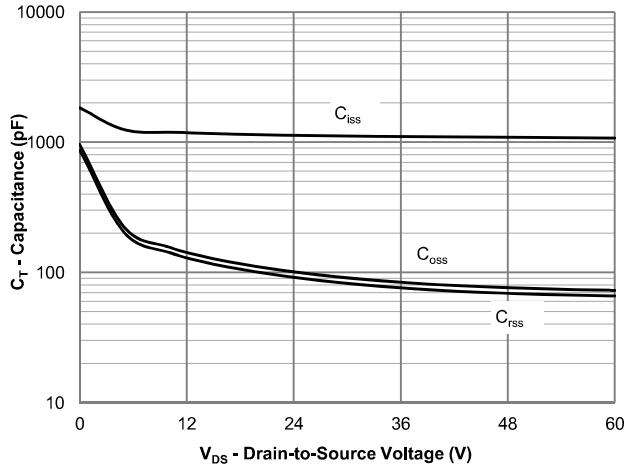


Figure 7: Capacitance Characteristics

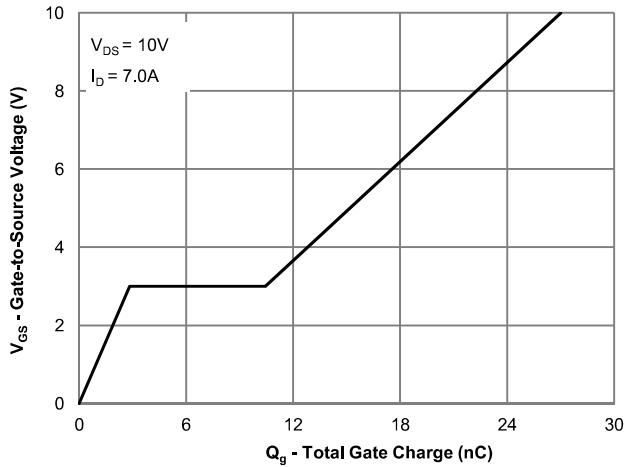


Figure 8: Gate Charge Characteristics

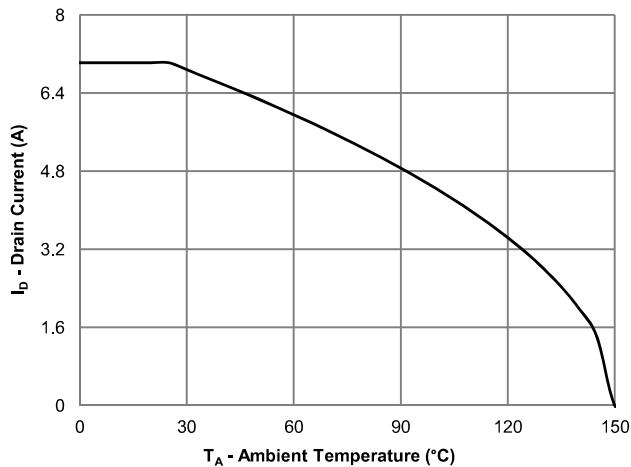


Figure 9: Current Derating

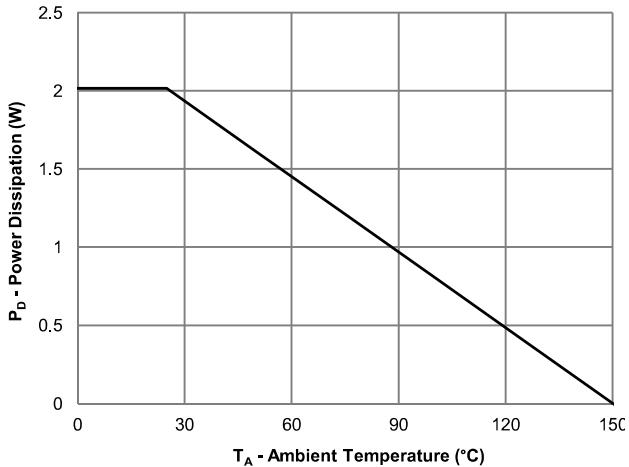


Figure 10: Power Derating

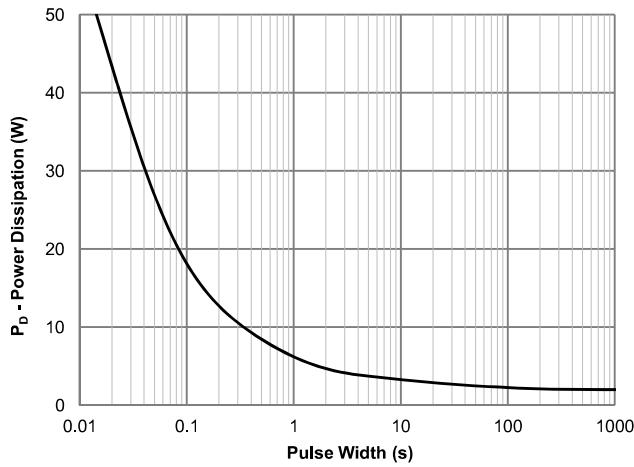


Figure 11: Single Pulse Power, Junction-to-Ambient

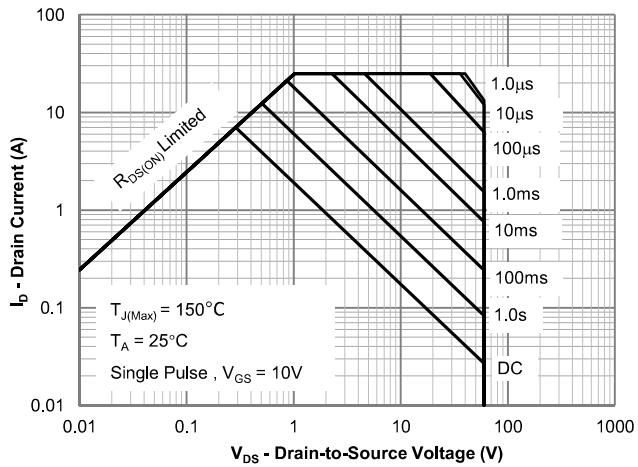


Figure 12: Safe Operating Area

**Typical Characteristics** (@  $T_J = 25^\circ\text{C}$ , unless otherwise specified.)

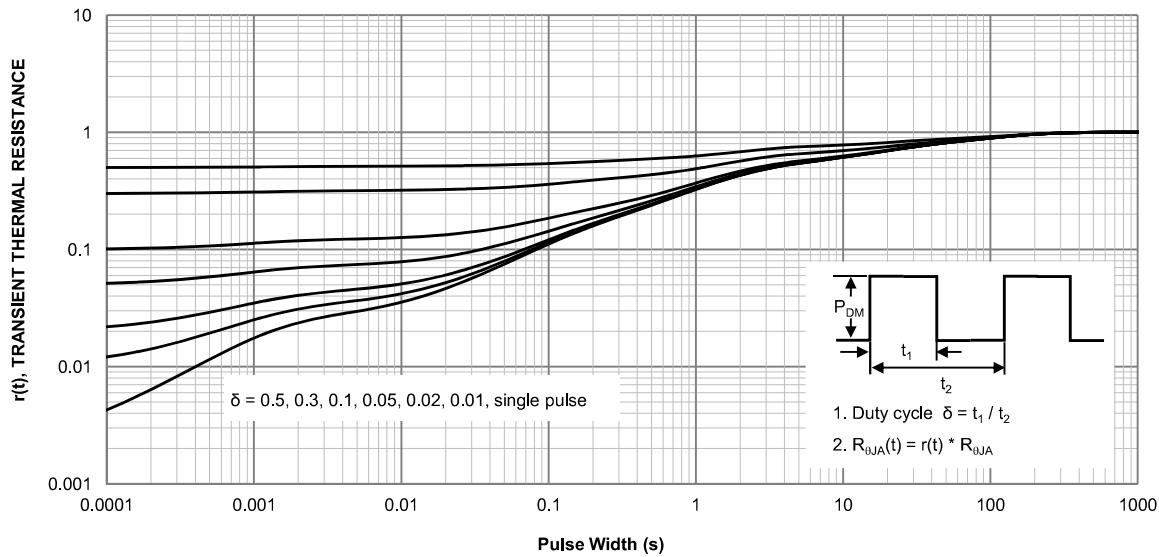
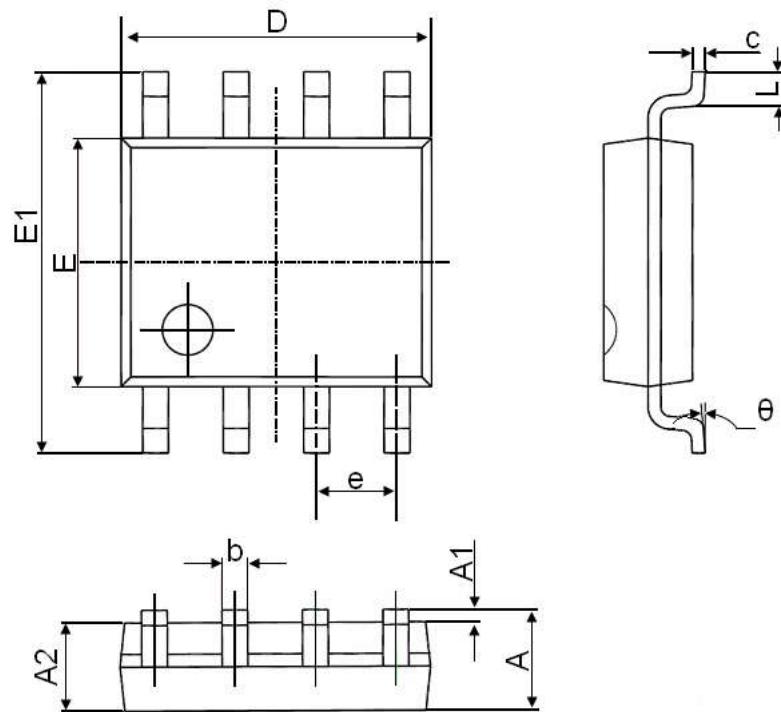


Figure 13: Normalized Thermal Transient Impedance

## SOP-8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°